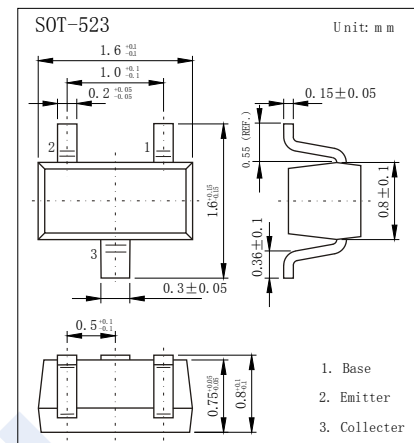


PNP Transistors

2SA1774

■ Features

- Reduces Board Space
- High h_{FE}
- Low $V_{CE(sat)}$

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-60	V
Collector - Emitter Voltage	V_{CEO}	-50	
Emitter - Base Voltage	V_{EBO}	-6	
Collector Current - Continuous	I_C	-150	mA
Collector Power Dissipation	P_C	150	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_C = -50 \mu\text{A}$, $I_E = 0$	-60			V
Collector- emitter breakdown voltage	V_{CEO}	$I_C = -1 \text{ mA}$, $I_B = 0$	-50			
Emitter - base breakdown voltage	V_{EBO}	$I_E = -50 \mu\text{A}$, $I_C = 0$	-6			
Collector-base cut-off current	I_{CBO}	$V_{CB} = -60 \text{ V}$, $I_E = 0$			-100	nA
Emitter cut-off current	I_{EBO}	$V_{EB} = -6 \text{ V}$, $I_C = 0$			-100	
Collector-emitter saturation voltage (Note.1)	$V_{CE(sat)}$	$I_C = -50 \text{ mA}$, $I_B = -5 \text{ mA}$			-0.5	V
Base - emitter saturation voltage (Note.1)	$V_{BE(sat)}$	$I_C = -50 \text{ mA}$, $I_B = -5 \text{ mA}$			-1.2	
DC current gain	h_{FE}	$V_{CE} = -6 \text{ V}$, $I_C = -1 \text{ mA}$	120		560	
Collector output capacitance	C_{ob}	$V_{CB} = -12 \text{ V}$, $I_E = 0 \text{ mA}$, $f = 1 \text{ MHz}$		3.5	5	pF
Transition frequency	f_T	$V_{CE} = -12 \text{ V}$, $I_C = -2 \text{ mA}$, $f = 30 \text{ MHz}$		140		MHz

■ Classification of h_{FE}

Type	2SA1774-Q	2SA1774-R	2SA1774-S
Range	120-270	180-390	270-560
Marking	FQ	FR	FS

PNP Transistors

2SA1774

■ Typical Characteristics

